

# Emitter common (dual digital transistors)

## EMG8 / UMG8N / FMG8A

### ●Features

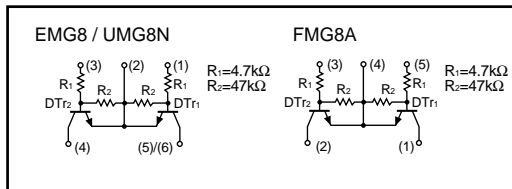
- 1) Two DTC143Z chips in a EMT or UMT or SMT package.
- 2) Mounting cost and area can be cut in half.

### ●Structure

Epitaxial planar type  
NPN silicon transistor  
(Built-in resistor type)

The following characteristics apply to both the DTr1 and DTr2.

### ●Equivalent circuit



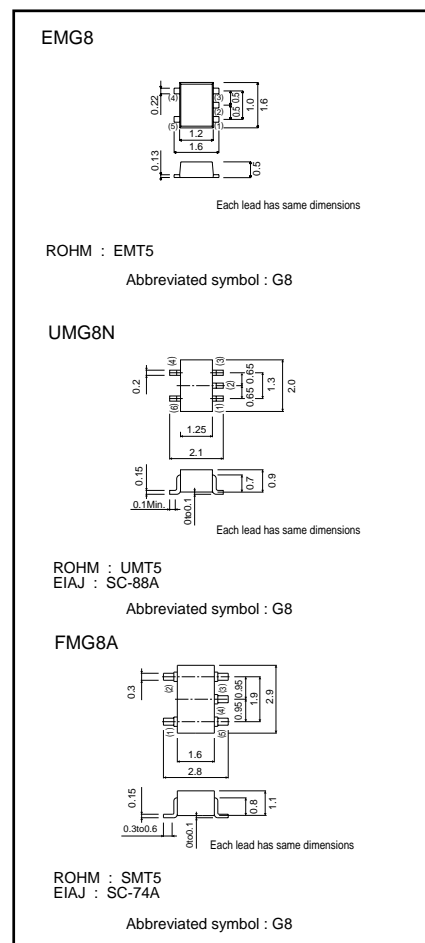
### ●Absolute maximum ratings (Ta = 25°C)

| Parameter            | Symbol                | Limits      | Unit |
|----------------------|-----------------------|-------------|------|
| Supply voltage       | V <sub>CC</sub>       | 50          | V    |
| Input voltage        | V <sub>IN</sub>       | 30          | V    |
|                      |                       | -5          |      |
| Output current       | I <sub>o</sub>        | 100         | mA   |
|                      | I <sub>c</sub> (Max.) | 100         |      |
| Power dissipation    | EMG8, UMG8N           | 150 (TOTAL) | mW   |
|                      | FMG8A                 | 300 (TOTAL) |      |
| Junction temperature | T <sub>j</sub>        | 150         | °C   |
| Storage temperature  | T <sub>stg</sub>      | -55~+150    | °C   |

\*1 120mW per element must not be exceeded.

\*2 200mW per element must not be exceeded.

### ●External dimensions (Units : mm)



Transistors

●Electrical characteristics (Ta = 25°C)

| Parameter            | Symbol       | Min. | Typ. | Max. | Unit      | Conditions                          |
|----------------------|--------------|------|------|------|-----------|-------------------------------------|
| Input voltage        | $V_{I(off)}$ | —    | —    | 0.5  | V         | $V_{CC}=5V, I_o=100\mu A$           |
|                      | $V_{I(on)}$  | 1.3  | —    | —    |           | $V_o=0.3V, I_o=5mA$                 |
| Output voltage       | $V_{O(on)}$  | —    | 0.1  | 0.3  | V         | $I_o=5mA, I_i=0.25mA$               |
| Input current        | $I_i$        | —    | —    | 1.8  | mA        | $V_i=5V$                            |
| Output current       | $I_{O(off)}$ | —    | —    | 0.5  | $\mu A$   | $V_{CC}=50V, V_i=0V$                |
| DC current gain      | $G_i$        | 80   | —    | —    | —         | $V_o=5V, I_o=10mA$                  |
| Transition frequency | $f_T$        | —    | 250  | —    | MHz       | $V_{CE}=10mA, I_e=-5mA, f=100MHz$ * |
| Input resistance     | $R_i$        | 3.29 | 4.7  | 6.11 | $k\Omega$ | —                                   |
| Resistance ratio     | $R_z/R_i$    | 8    | 10   | 12   | —         | —                                   |

\* Transition frequency of the device

●Packaging specifications

| Type  | Package                      | Taping |      |      |
|-------|------------------------------|--------|------|------|
|       | Code                         | T2R    | TR   | T148 |
|       | Basic ordering unit (pieces) | 8000   | 3000 | 3000 |
| EMG8  | ○                            | —      | —    | —    |
| UMG8N | —                            | ○      | —    | —    |
| FMG8A | —                            | —      | —    | ○    |

●Electrical characteristic curves

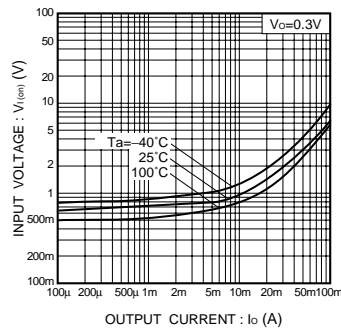


Fig.1 Input voltage vs. output current (ON characteristics)

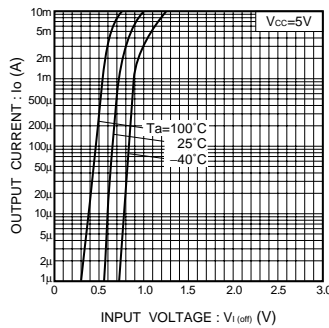


Fig.2 Output current vs. input voltage (OFF characteristics)

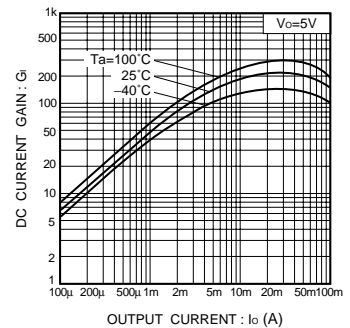


Fig.3 DC current gain vs. output current

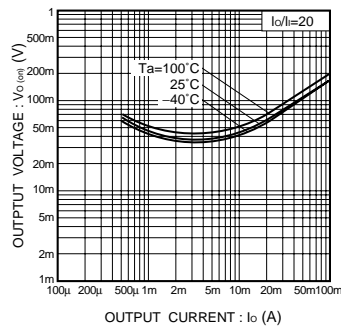


Fig.4 Output voltage vs. output current